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ZXMN15A27K

150V N-CHANNEL ENHANCEMENT MODE MOSFET

100% Unclamped Inductive Switch (UIS) test in production

High avalanche energy pulse withstand capability

"Green" component and RoHS Compliant (Note 1) Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic "Green" Molding Compound,

Terminals: Matte Tin Finish annealed over Copper leadframe.

UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208

Terminal Connections: See Diagram

Features and Benefits

Low input capacitance Low on-resistance Fast switching speed

Mechanical Data

Case: TO252-3L

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
150V	650mΩ @ VGs = 10V	2.6A

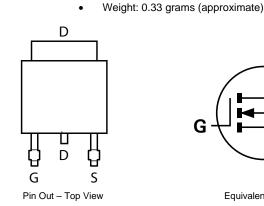
Description and Applications

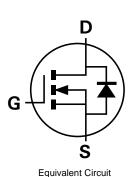
This MOSFET features low on-state resistance, fast switching and high avalanche withstand capability, making it ideal for high efficiency power management applications.

TO252-3L

Top View

- SLIC line drivers for VoIP applications
- **Transformer Driving Switch**
- Power management functions
- Motor control
- Uninterrupted power supply



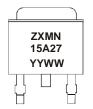


Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN15A27KTC	See Below	13	16	2,500

1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information Notes: about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMN = Product Type Marking Code, Line 1 15A27 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Last two digits of year (ex: 09 = 2009) WW = Week (01-52)



Maximum Ratings @T_A = 25°C unless otherwise specified

Chara	cteristic		Symbol	Value	Unit
Drain-Source voltage			V _{DSS}	150	V
Gate-Source voltage			V _{GS}	±25	V
Single Pulsed Avalanche Energ	у	(Note 7)	E _{AS}	55	mJ
Single Pulsed Avalanche Energ	Single Pulsed Avalanche Energy		I _{AS}	4.3	А
Repetitive Avalanche Energy		(Note 4)	E _{AR}	3.0	mJ
Repetitive Avalanche Current		(Note 4)	I _{AR}	4.3	А
Continuous Drain current		(Note 3) T _A = 70°C (Note 3) (Note 2)	ID	2.55 2.0 1.7	А
Pulsed Drain current	ulsed Drain current $V_{GS} = 10V$ (Note 4)		I _{DM}	17.2	А
Continuous Source current (Body diode)		(Note 2)	Is	5.2	А
Pulsed Source current (Body diode)		(Note 4)	I _{SM}	17.2	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
	(Note 2)		4.2 33.6		
Power dissipation Linear derating factor	(Note 3)	P _D	9.5 76.0	W mW/°C	
	(Note 6)	_	2.2 17.2		
	(Note 2)		30.2		
Thermal Resistance, Junction to Ambient	(Note 3)	R _{0JA}	13.1	°C/W	
	(Note 6)		58.1		
Thermal Resistance, Junction to Lead	(Note 5)	R _{θJL}	2.06	°C/W	
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C	

Notes: 2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions. The device is measured when operating in a steady-state condition.

3. Same as note 2, except the device is measured at t \leq 10 sec.

4. Same as note 2, except the device is operating in a repetitive state with pulse width and duty cycle limited by maximum junction temperature.

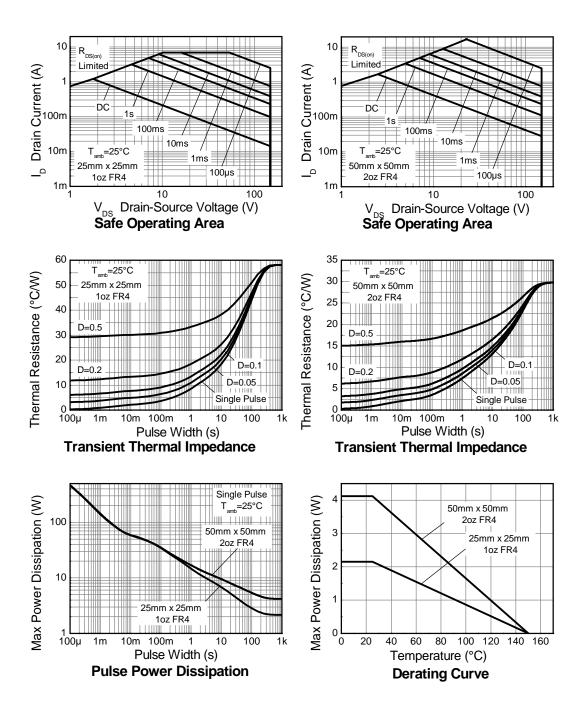
5. Thermal resistance from junction to solder-point at the end of the drain lead.

6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

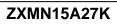
7. UIS in production with L = 5.95mH, I_{AS} = 4.3A, R_G = 25 Ω , V_{DD} = 100V, starting T_J = 25°C.



Thermal Characteristics







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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	<u> </u>		i	1		I	
Drain-Source Breakdown Voltage	BV _{DSS}	150		—	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}			500	nA	$V_{DS} = 150V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS}=\pm 25V,V_{DS}=0V$	
ON CHARACTERISTICS						-	
Gate Threshold Voltage	V _{GS(th)}	2	2.7	4	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	R _{DS (ON)}	—	0.500	0.650	Ω	$V_{GS} = 10V, I_D = 2.15A$	
Forward Transconductance (Notes 8 & 9)	g _{fs}		2.8		S	$V_{DS} = 40V, I_D = 2.15A$	
Diode Forward Voltage (Note 8)	V _{SD}		0.880	0.950	V	$I_{S} = 4.3A, V_{GS} = 0V$	
Reverse recovery time (Note 9)	t _{rr}		153		ns	I _S = 5.4A, V _{GS} = 0V, di/dt = 100A/μs	
Reverse recovery charge (Note 9)	Qrr	_	1.1	_	μC		
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}		169	_	pF		
Output Capacitance	C _{oss}		64.5		pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}		23.3	—	pF		
Total Gate Charge	Qg		6.6		nC	V _{DS} = 120V, V _{GS} = 10V - I _D = 5.4A	
Gate-Source Charge	Q _{gs}	_	1.0	_	nC		
Gate-Drain Charge	Q _{gd}	_	3.4		nC		
Turn-On Delay Time (Note 10)	t _{D(on)}	_	3.3		ns		
Turn-On Rise Time (Note 10)	tr	_	12.7		ns	V _{DD} = 75V, V _{GS} = 10V	
Turn-Off Delay Time (Note 10)	t _{D(off)}		17.1		ns	I_D = 5.4A, $R_G \cong 25\Omega$	
Turn-Off Fall Time (Note 10)	tf	_	13.3		ns		

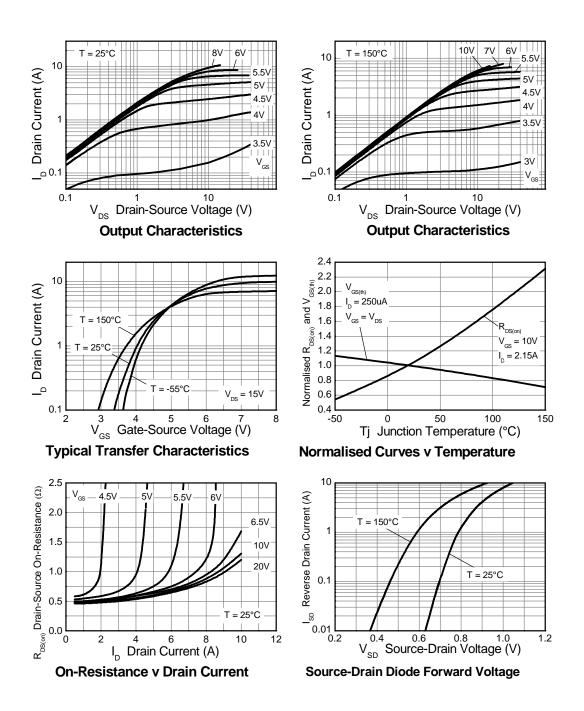
8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%$

9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures.

Notes:

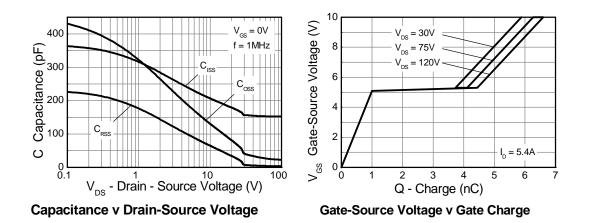


Typical Characteristics

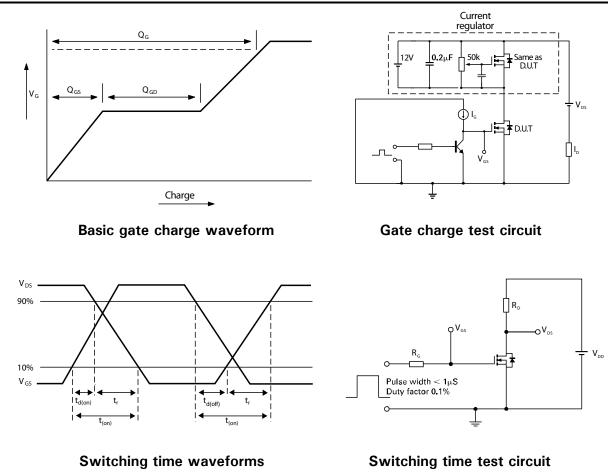




Typical Characteristics - continued

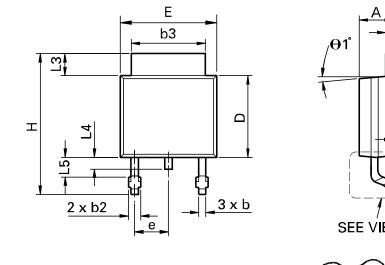


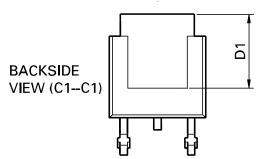
Test Circuits

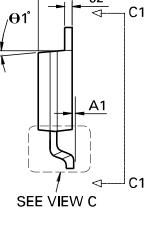




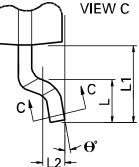
Package Outline Dimensions







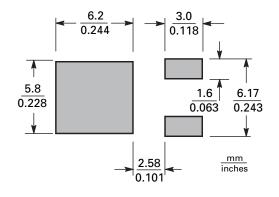
c2



DIM	Inc	hes	Millin	neters	DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
Е	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-



Suggested Pad Layout



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